

ISPSD 2018

CALL FOR PAPERS



CHICAGO, USA

The IEEE International Symposium on
Power Semiconductor Devices and ICs

Celebrating **30 YEARS** of Excellence in Advancing Power Semiconductor Technologies

ISPSD is the premier forum for technical discussions in all areas of power semiconductor devices and power integrated circuits, including but not limited to device physics, modeling, design, fabrication, materials, packaging and integration, device reliability, and device/circuit interactions. ISPSD 2018 will be held in the historic Palmer House Hilton Hotel, downtown Chicago, USA.

Main categories of interest include:

- **High Voltage Power Devices:** High voltage silicon based discrete devices ($> 200V$)
- **Low voltage devices and power IC device technology:** Low voltage silicon based discrete power devices ($\leq 200V$) and power devices for power ICs for all voltage ranges
- **Power IC design:** Circuit design and demonstration using power IC technology platform
- **GaN and nitride base compound materials – Device and technology:** GaN and nitride based power devices technology and integration, materials, and processing
- **SiC and other materials – Device and technology:** SiC and other material base power devices technology and integration
- **Module and Package Technologies:** Module and Package technology for discrete power devices and power ICs

Prospective authors should visit the ISPSD 2018 website: www.ispsd2018.com. A PDF abstract should be submitted through this website including a single-page text summary in English (500 words maximum) and up to two additional pages of supporting figures.

VENUE:

Palmer House Hilton

May 13-17, 2018

ISPSD2018.COM

Abstract submission deadline:

October 15, 2017

Author notification:

December 22, 2017

Late News submission deadline (limited acceptance):

March 1, 2018

Final manuscript submission deadline:

March 15, 2018

General Chair:

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ISPSD 2018 is sponsored by the IEEE Electron Device Society (EDS) and technically co-sponsored by the IEEE Power Electronics Society (PELS) and the IEEE Industry Applications Society (IAS)

